# E lectron-electron interactions and the phase diagram of a graphene bilayer

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W e study the e ects of long and short-range electron-electron interactions in a graphene bilayer. U sing a variational wavefunction technique we show that in the presence of long-range C oulom b interactions the clean bilayer is always unstable to electron and hole pocket form ation with a nite ferrom agnetic polarization. Furtherm ore, we argue that short-range electron-electron interactions lead to a staggered orientation of the ordered ferrom agnetic m om ent in each layer (that is, c-axis antiferrom agnetism). We also comment on the e ects of doping and trigonal distortions of the electronic bands.

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## I. IN TRODUCTION

The recent developm ents in the eld of carbon physics, where a few layers or even single layers of graphene have been isolated, have shown that the physics of these systems is unconventional from the point of view of traditional sem iconductor and Ferm i-liquid physics<sup>1,2</sup>. The electronic dispersion of graphene close to the two K – points of the Brillouin zone can be written as<sup>3</sup>: E (p) =

 ${\bf \psi}$  jpj where  $v_F$  is D irac-Ferm i velocity (this expression is valid for two-dimensionalmomentum p =  $(p_x;p_y)$  such that jpj < where is a momentum cut-o of the order of the inverse of the lattice spacing a). This dispersion relation is identical to the one of D irac electrons with <code>speed</code> of light" given by  $v_F$ . In this case the electron electrive mass, m, is zero, and the density of states vanishes at the K-point. The vanishing of the effective mass, the interplay of interactions, disorder, and extended defects, lead to anom alous behavior in many physical properties  $^{4,5}$ .

The capability of experimentally controlling the number of graphene layers opens up the ekd for the study of the e ect of interlayer coupling in a strongly interacting two-dimensional system. Interlayer coupling is a controversial topic in the graphite literature where the precise nature of the coupling between graphene planes is unsettled<sup>6,7</sup>. Another important issue in carbon research has to do with the weak ferrom agnetism in highly disordered graphite that have been observed in experiments<sup>8</sup> but is still a theoretically open problem <sup>9,10</sup>.

It is well-known that the low-density electron gas with long-range C oulom b interactions in two and three dim ensions is unstable tow and a ferrom agnetic state. The original argument due to B both relies on a variational calculation of the ground state energy<sup>11</sup>. Recently this approach was used to look for a possible ferrom agnetic instability in a single layer of graphene<sup>10</sup>. The parameter that controls the relative strength between kinetic and C oulom b energies is the dimensionless coupling,  $g = e^2_{0} = 1 = V_F$ ; (h = 1) where e is the electric charge ( $e^2 = 14:4 \text{ eV A}$ ),

and  $_0$  is the graphene dielectric constant ( $_0$  1). In that case, ferrom agnetism is only found for values of g larger than a critical value,  $g_c$  5:3, which is larger than its estimated value in graphene (g 2:1). An analysis based on short-range interactions seems to con m this picture<sup>5</sup>.

In this paper we use a sim ilar variational technique to study a clean graphene bilayer where we include the hopping between graphene planes. Unlike the case of a single layer, we distribute not be always unstable toward a ferrom agnetic state with form ation of electron and hole pockets with a polarization of the order of 10<sup>-6</sup> to 10<sup>-5</sup> electrons per carbon. This result may have direct in plications for the interpretation of the magneto-transport data in graphitic devices<sup>12</sup>.

The paper is organized as follows: In Section II the model is introduced. In Section III we explain the variational calculation and present the phase diagram. The in uence of other hopping parameters on the instability are discussed in Section IV. Section V includes the results for the low-energy susceptibilities and a discussion of short range interactions. The conclusions of the paper are to be found in Section V I. We also include appendices with some m athem atical details.

# II. THE MODEL

The lattice structure for the bilayer which is just one unit cell of graphite is depicted in Fig. 1. For simplicity we model the system by the nearest neighbor tightbinding H am iltonian:

$$H_{t.b.} = t X_{(C_{A_{1},m}^{V}; C_{B_{1},n}; + h.c.)}$$

$$X_{i;}^{(m,n)} X_{(C_{A_{1},m}^{V}; C_{A_{2},m}; + h.c.);} (1)$$

$$m;$$

where  $c_{a_1,m}$ ;  $(c_{a_1,m}^{\forall}; )$  annihilates (creates) an electron on site m of the sublattice a (a = A;B) of plane i

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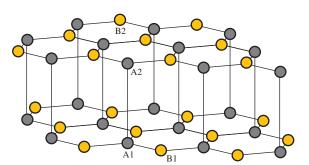


FIG.1: (Color online) Lattice structure of the bilayer. The A-sublattices are indicated by the darker spheres.

(i = 1;2), with spin (=";#), t (t 3 eV) is the inplane hopping energy and t; (t; 0:35 eV in graphité) is the hopping energy between atom A<sub>1</sub> and atom A<sub>2</sub> (see Fig. 1). A sim ilar tight-binding H am iltonian for graphite and the single graphene layer was studied long ago by W allace<sup>3</sup>. At low energies and long wavelengths, the kinetic H am iltonian can be expanded around the K (K') points in the Brillouin zone. The resulting H am iltonian can be written as:

$$H_{kin} = \bigvee_{Q}^{Y} K(p) Q; \qquad (2)$$

$$K (p) = \begin{bmatrix} 0 & pe^{i(p)} & t & 0 \\ B & pe^{i(p)} & 0 & 0 & 0 \\ C & t & 0 & 0 & pe^{i(p)}A \\ C & t & 0 & 0 & pe^{i(p)}A \end{bmatrix}$$
(3)

is the kinetic energy matrix where (p) = tan  ${}^{1}$  (p<sub>y</sub>=p<sub>x</sub>). We have set  $v_F = 1 = ...$ , so that the energy is measured in units of the in-plane hopping, t, and distance is measured in units of carbon-carbon distance a (a 1:42 A)<sup>6</sup>.

The kinetic term can be diagonalized by a unitary transformation:  $_{p} = M_{p} _{pp}$ , where  $M_{p}$  is given in Appendix A. Then  $H_{kin} = _{p;j; a} E_{j}(p) _{p;j; a}^{y} _{p;j; a}$ , where the four energy bands are given by:

$$E_{1}(p) = t_{2} = 2 + E(p);$$

$$E_{2}(p) = t_{2} = 2 E(p);$$

$$E_{3}(p) = t_{2} = 2 + E(p);$$

$$E_{4}(p) = t_{2} = 2 E(p);$$

where E (p) =  $\frac{P}{t_2^2 = 4 + p^2}$ . The bands are sketched in Fig. 2. Any state of the system can be labeled in terms of the occupation of each band,  $n_{i_1; i_2}$  (p), with

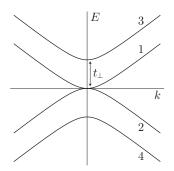


FIG. 2: Band dispersions near the K-points in the bilayer. Bands are labeled by the numbers 1 4 as in the text.

i = 1;2;3;4. The non-interacting ground state has degeneracy 4 permomentum, perplane, due to the SU (2) spin rotation symmetry and the  $Z_2$  real space sublattice exchange symmetry (at low energies this symmetry becomes SU (2) for the continuous rotation of the K and K' states in momentum space), and occupation at half-lling, given by:  $n_1$ ;  $_{ia}$  (p) = 0,  $n_2$ ;  $_{ia}$  (p) = 1,  $n_3$ ;  $_{ia}$  (p) = 0 and  $n_4$ ;  $_{ia}$  (p) = 1. Hence, the presence of t<sub>2</sub> does not m ix the spins or the K -points. However, the two D irac cones transform into vertex touching hyperbolae, and for p t<sub>2</sub> the electrons acquire an elective m ass, m t<sub>2</sub> = 2.

The Coulomb interaction in the bilayer is conveniently written in terms of the Fourier components of symmetric and anti-symmetric combinations of the layer densities,  $(q) = _1(q) _2(q)$ , where  $_i(q) = _P$ k; ; ,  $_a C_{k+q;i}^{y}$ ,  $_a c_{k;i}$ ; ,  $_a c_{k;i}$ ,  $_a c_{k;i}$ ,  $_a c_{k}$ ,  $_a c_{k+q;i}$ ,  $_a c_{k}$ ,

$$H_{I} = \frac{1}{2S} X X (q)V (q) (q); (4)$$

where V (q) = 2 e<sup>2</sup> (1 e q<sup>d</sup>)=2 Q, q, S is the area of the system, and d is the interplane distance (d 2:4a 3:35A, d 3:7). We are going to show that in the presence of Eq. (4) the non-interacting ground state is unstable. To perform the calculation it is convenient to express the density operators in the diagonal basis: (q) =  $p_{j;i;j;} = q_{p+q;i;} = q_{p+q;i;} = q_{p+q;i;} = q_{p+q;i;} = q_{p+q;i;}$ 

$$\frac{E_{ex}}{S} = \frac{1}{2} \frac{dp}{(2)^2} \frac{d^2p^0}{(2)^2} X$$

$$(p^0;p)_{ji}(p;p^0)n_{ij}; _{ja}(p^0)n_{jj}; _{ja}(p)V (p^0 p): (5)$$

The denitions of the matrices and some more details about the exchange interaction for B loch electrons and Eq. (5) are given in Appendix B.

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## III. VARIATIONAL CALCULATION AND PHASE DIAGRAM

Consider the half-lled case with a variational state with one electron pocket in the spin up channel and one hole pocket in the spin down channel at each K-point:  $n_{1;";a}(p) = (Q)$ p),  $n_{1;\#;a}(p) = 0$ ,  $n_{2;";a}(p) = 1$ , and  $n_{2;\#;a}(p) = 1$ (Q p), where Q, the size of the pocket, is a variational parameter (in what follows we assume t<sub>?</sub> and hence the occupations of bands 3 and 4 Ο are not a ected). Pictures of the non-interacting ground state and the trial state are shown in Fig. 3a and 3b. Notice that the size of the pocket is the same in di erent channels because of the conservation of the number of electrons at half-lling. This state breaks the SU (2), but not the Z2 sym m etry, and is therefore spin polarized (ferrom agnetic). There is a similar state that breaks both symmetries and has no net magnetization: an electron (hole) pocket in the up (down) spin channel in K-point 1 and a hole (electron) pocket in the up (down) channel in K-point 2.W e can show that the spin polarized state is lower in energy (see below).

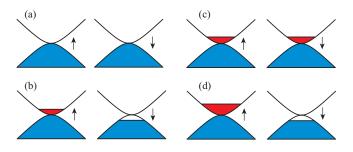


FIG. 3: (Color online) Sketch of the trial states: (a) Half-led non-interacting ground state, (b) Trial state with particle-hole pockets built upon (a), (c) Doped noninteracting ground state, (d) Trial state with particle-hole pockets built upon (c).

The change in the kinetic energy per unit area due to an electron (or hole) pocket of size Q is given by:

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$$\frac{E_{kin}}{S} = \frac{1}{2} \frac{(Q^2 + t_2^2 = 4)^{3=2}}{3} \frac{t_2^3}{24} \frac{t_2 Q^2}{4} \frac{Q^4}{8 t_2};$$
(6)

up to order Q<sup>4</sup>. The expressions for the change in the exchange energy are cum bersom e and details are provided in Appendix C. We differ Eq. 5, up to the same order:

$$\frac{E_{ex}(Q)}{S} = \frac{g}{8^2} \frac{g}{27} Q^3 = \frac{h}{3} \frac{3}{8} + \frac{1}{2} \ln (4 = t_2) = \frac{Z_1}{4} \frac{g}{0} \frac{e^{-d-y}}{t_2^2 = 4 + y^2} \frac{iQ^4}{t_2} = (7)$$

Notice that the leading order term in the exchange interaction is  $E_{ex}=S$   $gQ^3=27$   $^2$   $m^{3=2}$ , where m is the magnetization, which is always dominant over

the kinetic term that is of order Q<sup>4</sup> m<sup>2</sup>. Therefore, we have proved that the bilayer is always unstable to the form ation of polarized electron and hole pockets. In contrast to the single graphene plane case<sup>10</sup>, the total energy is negative for small Q. This is due to the fact that the exchange with the led bands is less in portant in this case. In order to calculate the equilibrium size of the pockets we minim ize the total energy,  $E_{tot}(Q) = E_{kin}(Q) + E_{ex}(Q)$ , with respect to Q and nd  $Q_{min}$ , that is, the size of the pocket for which the energy is minimized. For the parameters in graphene (see below) we nd that  $Q_{min}$  0.055 (t<sub>2</sub>), justifying the above expansion.

Consider the case where the system is initially doped with pockets of size  $Q_0$  (n =  $Q_0^2=2$ ). We look for an instability by varying the density of electrons and holes subject to the constraint of particle conservation. Note that the instability can produce one type of carrier (either electron or hole) if  $Q_0 > Q_{m in}$  or two type of carriers (electrons and holes) if Q  $_0$  < Q  $_m$  in . W e can param eterize the state with one type of carrier by taking  $Q_{\pi}^2 = Q_0^2$  (2) 1. For the state with x) and  $Q_{\#}^{2} = Q_{0}^{2} x \text{ with } 0$ х two types of carriers we take instead  $Q_{\mu}^{2} = 2Q_{0}^{2} + j_{x}j_{z}$ and  $Q_{\#}^{2} = j_{x} j_{y}$  with x 0. The doped non-interacting ground state and the trial state with particle-hole pockets (x < 0) are shown pictorially in Fig. 3c and 3d. The calculation proceeds as before and we nd:

$$\frac{E}{S} = \frac{1}{2S} = E_{tot}(Q_{*}) + E_{tot}(Q_{*}) = 2 = E_{tot}(Q_{0}) + E_{extra}(Q_{0};x): (8)$$

The extra term,  $E_{extra} (Q_0; x)$ , comes from terms that cancel out in the undoped case. To leading order in Q these terms are given by  $gQ_0^4 (1 x)^2 = (64)$  for x = 0 and  $gQ_0^2 (Q_0^2 + 2jx) = (64)$  when x = 0. In our units we have  $t_2$  1 so that, to a rst approximation, this contribution is much smaller than the quartic term in Eq. (7), and it can be neglected. This leaves us with the rst line in Eq. (8) involving  $E_{tot}$  only. The dependence on x is implicit through  $Q_*$  and  $Q_{\#}$ . Then Eq. (8) has the form:  $E(Q) = AjQ_j^2 + BjQ_j^4$ . Rescaling the Q variable so that the minim a of the energy in the param agnetic states sits at  $jQ_j = 1$ , we have:

$$E(Q) = jQj = 3 + jQj = 4:$$
 (9)

U sing the scaled variables we see that the system is unstable to small deviations in x from 1 if  $Q_0$  1=2. The ferrom agnetic state has lower energy than the param – agnetic states if  $Q_0 \leq 0.7$  and the resulting state has electron and hole pockets. As a consequence of the rst order nature of the transition, the system exhibits phase coexistence (that can be obtained from a M axwell construction, not shown in the Fig. 4), and hysteresis in physical properties such as magneto-transport, around the critical line. In this region, the system shows a tendency towards electronic phase separation<sup>13</sup>, frustrated by electrostatic e ects. As the charge densities involved are rather low (see below) we cannot exclude the form ation of large dom ains of the di erent phases. The phase diagram for  $t_2 = 0.05$  is shown in Fig. 4 as well as a plot of E (Q<sub>0</sub>;x) for some typical cases of Q<sub>0</sub>.

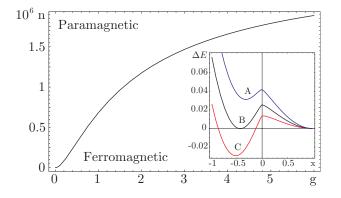


FIG.4: (Color online) Left: Phase diagram of the graphene bilayer as a function of electron density away from half-lling, n (electrons per carbon), and coupling strength,  $g = e^2 = (\ _0 v_F)$ , with  $t_2 = 0.05$ . Inset: E as a function of x (as de ned in the text) in the paramagnetic (A), critical (B), and ferrom agnetic (C) regions of the phase diagram.

In the previous calculation we have not included the exchange interaction between di erent K-points in the Brillouin zone. In that case the spin polarized state that breaks SU (2) is degenerate with the state that breaks both SU(2) and  $Z_2$ . The di erence between the states is how the pockets are assigned to the spins and the K-points. By including exchange between Kpoints in Eq. (5) we nd that there is small energy di erence between the states favoring a state with a net ferrom agnetism but which retains the Z2 symmetry. Quite generally this is the case since the elements of  $_{ij}(p^{0};p)$   $_{ji}(p;p^{0})$  are all positive. A direct calculation using Eq. (5) and taking p and  $p^0$  to lie at nearest neighboring K-points con msthis picture. One then nds a very small energy di erence of order /  $Q^4$ , and hence other e ects can be in portant in determ ining the actual ground state. There is also a correction to the  $Q^4 = t_2 - t_2$ term in Eq. (7) that changes the position of the optimal value of  $Q_{m in}$  by a sm all am ount.

In order to compare with experiments it is interesting to estimate the total magnetization in the polarized state for the case of the undoped graphene bilayer. W e estim ate the cut-o using a Debye approxim ation so the the number of states is conserved in the Brillouin zone:  $^{2} = 2 = A_{u} = 4 = (\overline{27}a^{2})$ , where  $A_{u}$  is the area of the real space unit cell. Restoring the units, we set  $v_F$  = 10<sup>2</sup>,  $10^{\circ} \text{ m/s}$ , and  $t_2 = 1 = (v_F)$ 52 3 ₀a=2 0:37 eV is the typical graphite value. Hence, where 1 for two pockets of size Q the density of electrons per carbon is approximately  $n = Q^2 = 4$  1:6 10<sup>6</sup> (t<sub>2</sub>) 0:05 0:05t ), and therefore, the magnetization per and O  $10^{6}$   $10^{5}$  <sub>B</sub> (<sub>B</sub> is the Bohrm agneton). carbon ism These number are, of course, very approximate because the value of the microscopic parameters do not need to be

the same as in graphite and the presence of a cut-o introduces further uncertainty. In any event, the magnetized state of the graphene bilayer shows very weak ferrom agnetism. A direct experimental consequence of our calculation is that the bilayer has two species of electrons (electrons and holes) and therefore they should contribute to the Hall resistivity at small magnetic elds, B. In particular, it is easy to show that the magneto-resistance at small magnetic elds acquires a B<sup>2</sup> dependence<sup>14</sup>.

## IV. OTHER HOPPING PARAMETERS

W ewould like to comment on other e ects that we have not considered in the previous calculation. In terms of the SlonczewskiW eiss M cC lure model for graphite<sup>15,16</sup> our model includes only the parameters  $_0$  (t) and  $_1$ (t<sub>?</sub>) but not  $_3$  and  $_4$ . On the one hand,  $_4$  introduces an electron-hole asymmetry by changing the curvature of the bands, but the bands remain parabolic near half

lling. On the other hand,  $_3$  introduces a trigonal distortion which restores a linear dispersion at low energies. To estimate the e ects of  $_3$  we use the e ective low – energy model that can be derived from the extension of Eq. (3) to include  $_3$  and projecting onto the two bands that are closest to the Ferm i surface (see Ref. [17] and Appendix E for details). The e ective kinetic energy m atrix is then:

$$K(p) = \frac{p^2}{t_2} e^{i2} 0 + v_3 p e^{i} 0 ; (10)$$

where  $v_3 = 3 = 0$ , with energy eigenvalues given by:

E (p) = 
$$p \frac{p}{p^2 + (v_3 t_2)^2 + 2pv_3 t_2 \cos[3(p)]} = (11)$$

It is easy to see that the crossover from linear to quadratic dispersion takes place at a momentum pcross v₃t₂. If p<sub>cross</sub>  $Q_{m in}$  ( $v_3$ 0:1) the previous calculation is still valid since the dispersion remains parabolic at the scale of the instability. Nevertheless, if one uses the values of the param eters in the graphite literature<sup>6</sup>, nam ely,  $v_3 = 3 = 0$ 0:1 we conclude that  $p_{cross}$   $Q_{m in}$  and the trigonal distortion may become important. We should remark, once again, that it is not guaranteed that the value of the parameters in graphite are the same as in the bilayer (hence, one should take the numbers here with a grain of salt). At sm all energies, the spectrum in Eq. (10) can be described in terms of one Dirac cone at p = 0, and three asymmetric cones at  $p_{cone} = v_3 t_2$ ? (the direction of the cones are such that  $\cos(3) = 1$ ). T his situation m aps onto the single graphene plane  $case^{10}$ with ellipsoidal pockets instead of circular, and a small renorm alized Ferm ivelocity, v<sub>F</sub>  $v_{S}v_{F}$  (  $v_{F}$ ). Therefore the dimensionless coupling strength is  $q = q = v_3$ 20, which is much larger than the critical coupling for ferrom agnetism<sup>10</sup>. Then, in this case the transition from param agnetism is into a fully polarized state with e ective bandwidth of order of  $v_3 t_2$ , leading to a polarization

of the order of 10  $^{6}$  electrons per carbon, which is of the same order of magnitude of polarization found without  $_{3}$ . Unfortunately this argument is not rigorous since the exchange with the led bands also contributes, requiring a more detailed study.

# V. SHORT RANGE INTERACTIONS

W e consider the e ects of short-range electron-electron interactions which, for sim plicity, we describe by an onsite H ubbard interaction, U. It turns out that this interaction favors an antiferrom agnetic ordering. In order to quantify the tendency towards this phase, we calculate the associated susceptibility and present a sim ple m ean eld argum ent.

### A. Electronic susceptibility.

U sing the basis de ned in Eq. (10) with  $v_3 = 0$  (the procedure outlined in Appendix E) the wavefunctions corresponding to the two bands closest to the Ferm i level can be written approximately as:

(k) 
$$\frac{1}{P_{\frac{1}{2}}} \stackrel{e^{i(k)}}{e^{i(k)}};$$
 (12)

so that the states are mostly localized at the sites without a corresponding atom in the neighboring layer. Formally, this two component wavefunction is equivalent to the spinor de ned in the analysis of a single graphene plane except that the angle is doubled. Restricting the calculation to this subspace, we can write the bare susceptibility as a  $2 \mod 2 \mod 2 \mod 2$ .

$${}_{0}(q;!) = {}_{ND}(q;!) {}_{D}(q;!) {$$

Here  $_{\rm D}$  denotes the response in the same plane as the source and  $_{\rm ND}$  response in the opposite plane. The random phase approximation (RPA) susceptibility, assum - ing an on-site Hubbard interaction U, is:

$$_{RPA}(q;!) = _{0}(q;!) 1 U_{0}(q;!)^{\perp}: (14)$$

This expression becomes simpler when decomposed into a contribution symmetric in the two sublattices and another antisymmetric:

$$\frac{\frac{FM}{4}(q;!)}{4} = \frac{D}{1}(q;!) + ND(q;!)}{1};$$

$$\frac{AFM}{4}(q;!) = \frac{D}{1}(q;!) + ND(q;!)}{1}(q;!) + ND(q;!)}{1}(15)$$

The symmetric susceptibility gives the response of the system to a magnetic eld which is the same in the two sublattices (note that we are neglecting the in uence of the sites where the states have zero weight of k = 0), and induces a ferrom agnetic ordering. The antisymmetric response leads to antiferrom agnetic ordering. The susceptibilities can be written as:

where k+q=2, k=q=2 is the angle between k+q=2 and k=q=2, and:

$$\cos^{2} \quad _{k+q=2;k-q=2} = \frac{(k+q=2)}{j_{k}+q=2j_{k}} \quad (k \quad q=2j_{k}) = \frac{(k^{2} \quad q^{2}=4)^{2}}{(k^{2}+q^{2}=4)^{2} \quad k^{2}q^{2}\cos^{2}(x)}$$
(17)

The only dependence on the angle between the vectors k and q of the expressions in Eq. (16) is (after using the double angle form ula) through the cosine in Eq. (17). A veraging over angles, we obtain:

$$\cos^{2} \quad _{k+q=2;k} \quad _{q=2} \quad = \quad \frac{k j^{2} \quad j q^{2} = 4}{j k j^{2} + j q j^{2} = 4} \quad : \tag{18}$$

Inserting this expression into Eq. (16) it is a simple task to perform the remaining one-dimensional integral. Introducing  $^{0}_{FM} = _{D} (q;!) + _{ND} (q;!)$  and  $^{0}_{AFM} = _{D} (q;!) _{ND} (q;!)$  we can extract the leading dependence on the cut-o of the susceptibilities, and we nally obtain:

$$\operatorname{Re}_{FM}^{0}(q;!) = \frac{1}{4} \sum_{s=1}^{X} \operatorname{h}_{t_{2}} \ln \frac{\dot{n}\dot{f}}{\dot{n}\dot{f}^{2}=2} \frac{s!\,\mathfrak{t}}{s!\,\mathfrak{t}} + \frac{\dot{n}\dot{f}}{2s!} \ln \frac{2\dot{n}\dot{f}}{\dot{n}\dot{f}^{2}=2} \frac{2\,\mathfrak{n}!\,\mathfrak{t}}{s!\,\mathfrak{t}} 2\,\operatorname{ln}\frac{\dot{n}\dot{f}}{\dot{n}\dot{f}^{2}=2} \frac{s!\,\mathfrak{t}}{s!\,\mathfrak{t}}^{i},$$

$$\operatorname{Re}_{AFM}^{0}(q;!) = \frac{\mathfrak{t}_{2}}{8} \sum_{s=-1}^{X} \ln \frac{2^{2}}{\dot{n}\dot{f}^{2}=2} \frac{s!\,\mathfrak{t}}{s!\,\mathfrak{t}} \operatorname{Re}_{FM}^{0}(q;!);$$

$$\operatorname{Im}_{FM}^{0}(q;!) = \frac{\mathfrak{t}_{2}}{4} \operatorname{ln} \frac{\dot{n}\dot{f}}{2j!\,\mathfrak{t}_{2}} \frac{j!\,j}{2\mathfrak{t}_{2}} \frac{\dot{n}\dot{f}}{2\mathfrak{t}_{2}} 1 \frac{\dot{n}\dot{f}}{j!\,\mathfrak{t}_{2}} j!\,j \frac{\dot{n}\dot{f}}{j!\,\mathfrak{t}_{2}} \frac{j!\,j}{\mathfrak{t}_{2}} \frac{\dot{n}\dot{f}}{\mathfrak{t}_{2}} \frac{i}{sign}(!);$$

$$\operatorname{Im}_{AFM}^{0}(q;!) = \frac{\mathfrak{t}_{2}}{8} j!\,j \frac{\dot{n}\dot{f}}{2\mathfrak{t}_{2}} \operatorname{sign}(!) \operatorname{Im}_{FM}^{0}(q;!):$$

$$(19)$$

Hence, setting q = 0, the antiferrom agnetic susceptibility diverges logarithm ically with the cut-o for any nite frequency !. The logarithm ic dependence in plies the existence of an instability for any positive value of the interaction U. A lternatively, we can show the existence of this instability by a direct calculation of the correlation energy gained by polarizing the system.

It is worth noting that the divergence obtained here, and the related marginal behavior of a local interaction can be obtained from the same power counting arguments used for the analysis of two dimensional interacting electrons near a van Hove singularity<sup>19</sup>. If we include next nearest neighbor couplings through the parameter <sub>3</sub>, as discussed in Section IV, the low energy bands can be described by an elective Dirac equation. The screening of the long range C oulom b interaction vanishes, and the corresponding susceptibility can also be calculated analytically<sup>20,21</sup>.

Note also that the polarization function is simply related to the susceptibilities<sup>22</sup> above by <sup>0</sup> = <sup>0</sup>. This allows one to get the screening properties within the RPA easily. In particular, for the mode that is sym – metric in the layer densities which originally had the long-wavelength 1=jqj singularity the static (! = 0) RPA screening cuts o the singularity by taking 1=jqj! 1=(jqj+q\_{TF}). From Eq. (19) we nd that the Thom as-Ferm i screening wavevector  $q_{TF}$  /  $t_2$ . This is in agreement with what one expects from the usual two-dimensional electron gas where the screening wave-vector is / m independently of the density of carriers<sup>23,24</sup>.

# B. M ean-eld approach

A lternatively we can explain the diverging susceptibility with a simple mean-eld approach. We introduce a staggered mean-eld into the Ham iltonian according to

$$K (p) = \begin{pmatrix} 0 & pe^{i(p)} & t_{2} & 0 \\ B & pe^{-i(p)} & 0 & 0 \\ 0 & t_{2} & 0 & pe^{-i(p)} \\ 0 & 0 & pe^{i(p)} \end{pmatrix}$$
(20)

where the label di errent spin orientations. The four bands are then:

(k) = 
$$\frac{2k^2 + t_2^2 + 2 \cdot 2}{2} = \frac{p}{4k^2 + t_2^2}$$
 (21)

The opening of the gap lowers the kinetic energy of the system . We estimate this by performing the integral up to k = 1, then for  $t_{2} = .05$ 

$$E_{kin}$$
 21:9043  $\frac{t_2}{2} \ln()^2 + O(^3);$  (22)

is the change in the kinetic energy per unit cell due to . The connection between the average magnetization  $M = j < n_{j;"} > < n_{j;\#} > j$  and the mean eld is = UM = 2, where U is the strength of the on-site Hubbard interaction. The energy price one must pay per unit cell for having doubly occupied sites is

$$E_U = UM^2 = \frac{4}{U}^2$$
: (23)

Because of the logarithm in Eq. (22) a small antiferrom agnetic distortion is always favorable. A ssum ing that is small, the mean-eld solution is:

<sub>MF</sub> exp 
$$\frac{1}{2}$$
  $\frac{2=U \ 1.9043}{t_2=2}$ ; (24)

and hence is exponentially suppressed unless U is of the order of .0 ther variations of the m ean- eld in Eq. (20) give sim ilar results. Thus within the m ean- eld approximation, the anti-ferrom agnetism found here is very weak unless the interaction is strong.

## VI. CONCLUSIONS

In sum m ary, we have show n that long-range C oulom b interactions in a clean graphene bilayer lead to a ground state that is m agnetically polarized with electron and hole pockets. We have determ ined the phase diagram of thism odelas a function of the coupling strength and doping, with a rst order phase transition line between the param agnetic and ferrom agnetic states. A round the critical line one expects hysteresis e ects associated with the presence of phase coexistence and/or m agnetic dom ains. We have also shown that on-site electron-electron interactions produce a staggering of the ferrom agnetic order in the two planes and hence, c-axis antiferrom agnetism. The introduction of other terms in the H am iltonian, such as trigonal distortions, m akes the phase diagram even richer, due to the creation of new energy scales. It is clear from our studies that graphene bilayers present an electronic behavior that is rather di erent from ordinary m etals. The study of these systems become seeven m ore relevant given the recent developments in the fabrication and control of graphene m ulti-layers, and their possible application in nano-electronics.

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## APPENDIX A: UNITARY TRANSFORMATION

The unitary transform ation M  $_{p}$  that one needs to diagonalize the H am iltonian in Eq. (3) can be written as M  $_{p} = M_{1}$  (p)M  $_{2}M_{3}$  (p), where

$$M_{1}(p) = \begin{cases} 0 & 1 & 0 & 0 & 1 \\ B & 0 & e^{i}(p) & 0 & 0 & C \\ 0 & 0 & 1 & 0 & A \\ 0 & 0 & 0 & e^{i}(p) \end{cases}$$
(A1)

is a gauge transform ation,

 $\cap$ 

$$M_{2} = \frac{1}{\frac{P}{2}} \begin{bmatrix} 0 & 1 & 0 & 1 \\ B & 0 & 1 & 0 & 1 \\ 0 & 1 & 0 & 1 \\ 0 & 1 & 0 & 1 \end{bmatrix}$$
(A 2)

form s sym m etric/antisym m etric bands, and

takes care of the nal diagonalizing rotation. Choosing  $\tan [2'(p)] = 2p=t_2$  the rotated H am iltonian  $K_{diag}(p) = M_p^y K(p) M_p$  becomes diagonal:

$$K_{diag}(p) = diag \quad t = 2 \quad E(p); \quad t = 2 + E(p);$$
  
 $t_2 = 2 + E(p); \quad t_2 = 2 \quad E(p): \quad (A 4)$ 

Except for the labeling of the states  $(1 \quad 4)$ , which is just a permutation, this is the unitary transform ation we need to diagonalize the non-interacting problem.

# APPENDIX B:EXCHANGE INTEGRAL FOR BLOCH ELECTRONS

Quite generally the Hartree-Fock energy consists of three term s. A kinetic term , a direct charging term , and an exchange term . The exchange term  $is^{25}$ 

where V is the interaction potential and the sum is over occupied states. Expanding in Bloch states  $k_i$ ; we get

$$E_{ex} = \sum_{\substack{k; \\ k^{0}; \\ k^{0}; \\ 0}}^{X} n_{k}; n_{k^{0}; 0}; J_{k;k^{0}};$$
(B2)

where for the unscreened C oulom b interaction in 2D

$$J_{k,k^{0}}^{; 0} = \frac{e^{2}}{2} \frac{Z}{d^{2}x} \frac{Z}{d^{2}x^{0}} \frac{e^{2}}{d^{2}x} \frac{Z}{d^{2}x^{0}} \frac{e^{2}}{\frac{k; (x)_{k^{0}; 0}(x)_{k^{0}; 0}(x^{0})_{k; 0}(x^{0})}{\frac{k}{jk} x^{0}j} : (B3)$$

Let us consider one plane only, then we can write the Bloch states in the tight-binding approximation as

$$_{k}; (x) = \begin{array}{c} X \\ e^{ik} & {}^{T_{A}} a_{k}; w (x & T_{A}) \\ & T_{A} \\ & + \begin{array}{c} X \\ e^{ik} & {}^{T_{B}} b_{k}; w (x & T_{B}); (B4) \end{array}$$

where w (x) is the localized basis function,  $T_A$  ( $T_B$ ) are the lattice vectors of lattice A (B) and  $a_k$ ; and  $b_k$ ; are the functions that generate the B loch state in question. N eglecting the overlap of wave-functions on the A and B sites we get approximately

The functions  $_{A}$  and  $_{B}$  are periodic in the real-space lattice and can hence be expanded in components of harmonics of the reciprocal lattice fK g. K exping only the leading constant term coming from the K = 0 terms we get = 1, in which case

$$J_{k,k_{0}}^{i} = a_{k}^{i}, a_{k_{0}}^{i}, a_{k}^{i}, b_{k}^{i}, b_{k_{0}}^{i}, a_{k}^{i}, b_{k}^{i}, b_{k}^{i}, \frac{2 e^{2}}{5 k k_{0}^{i}}; \quad (B 6)$$

The corrections to this K = 0 term are down by at least a factor of  $k^0 f$  as is explained in Ref. [25]. It is possible to include higher harm onics in the reciprocal lattice, but then the important divergence near  $k = k^0$  is cut-o by K. M oreover, including K  $\leq 0$  we should also include

short-range (high energy) physics that is not described by the continuum m odel used here.

Note also that the expression in Eq.  $(B \ 6)$  is just what one get from a simple Fourier transform if one also includes the spinor structure due to the two sub-lattices. W e apply this to the bilayer where the Coulom b interaction can be written

$$H_{I} = \frac{1}{2} \begin{bmatrix} Z & n \\ d^{2}x d^{2}y & V^{D}(x + y) & _{1}(x) & _{1}(y) + & _{2}(x) & _{2}(y) \\ + & V^{ND}(x + y) & _{1}(x) & _{2}(y) + & _{1}(x) & _{2}(y) \end{bmatrix} \stackrel{O}{:} (B7)$$

W e Fourier transform this and introduce the symmetric and antisymmetric combinations

$$(q) = {}_{1}(q) {}_{2}(q):$$
 (B8)

to write the interaction in a diagonal form

$$H_{I} = \frac{1}{2S} X^{0} X (q)V (q) (q); (B9)$$

where  $V = \frac{2 e^2}{oq} (1 e^{qd})=2$ . The prime on the q-sum denotes that the q = 0 term should be excluded since it is canceled by the positive (jellium) background. In terms of the operators that diagonalizes the kinetic terms the density operators can be written as

$$(q) = \sum_{p+q}^{X} (p+q;p)_{p}; \quad (B10)$$

where

and M  $_{\rm p}$  is given in Appendix A. Using this one can easily generalize Eq. (B2) and (B6) to arrive at Eq. (5).

# APPENDIX C:EXCHANGE INTEGRAL

Using  $V^{D}(q) = 2$  g=q and  $V^{ND}(q) = 2$  ge  $^{qd}$ =q one quite generally get that the change in the exchange energy can be written as

$$< \frac{H_{1}}{S} > = \frac{1}{2} \frac{dp}{(2)^{2}} \frac{dp^{0}}{(2)^{2}}^{n} 2 (Q p) K_{1}^{D} V^{D} + K_{1}^{ND} V^{ND} + (Q p) (Q p) K_{2}^{D} V^{D} + K_{2}^{ND} V^{ND}$$

The K 's are sum s of certain components of the m atrices  $_{ij}(p^{0};p) = _{ij}(p^{0};p) _{ji}(p;p^{0})$ . Note that the elements of are all greater or equal to zero. 1. H alf-lling

At half-lling the trial state is characterized by the single variational parameter Q. It is straightforward, albeit tedious, to perform the matrix multiplications and extract the K 's. The results for an electron and a hole pocket of size Q is:

$$K_{1}^{D} = \frac{p}{E(p)} \frac{p^{0}}{E(p^{0})} \cos(p^{0});$$
 (C2)

$$K_{1}^{ND} = \frac{t}{2E(p^{0})}^{n} 1 \frac{t}{E(p)} 1 + \frac{t}{E(p)} \cos 2(0);$$
 (C3)

$$K_{2}^{D} = \frac{1}{2} \frac{p}{E(p)} \frac{p^{0}}{E(p^{0})} \cos( ) + \frac{1}{2} 1 + \frac{t}{E(p)} \frac{t}{E(p^{0})};$$
(C 4)

$$K_{2}^{ND} = \frac{1}{2} \frac{p}{E(p)} \frac{p^{0}}{E(p^{0})} \cos( ^{0}) + \frac{1}{4} \frac{1}{4} \frac{t}{1} \frac{t}{E(p)} \frac{1}{E(p^{0})} + \frac{t}{E(p^{0})} \frac{t}{E(p^{0})} + \frac{t}{E(p)} \frac{t}{E(p^{0})} \cos^{2}( ^{0})^{\circ}: (C5)$$

In this appendix we temporarily relabel  $t_2 = 2$ ! to avoid an excessive amount of 2's in the equations. We can write

$$< \frac{H_{I}}{S} > = \frac{gv_{F}^{3}}{4^{2}} C_{1}^{D} + C_{1}^{ND} + C_{2}^{D} + C_{2}^{ND}$$
; (C6)

where we are measuring all parameters (i.e. Q and t) in units of the cut-o . The C's are given by the integrals

$$C_{1}^{D} = 2Q^{3} \frac{x \, dx}{x \, dx} \frac{y \, dy}{y \, dy} d \frac{p \frac{x}{t^{2} + (Q x)^{2}}}{p \frac{y^{2} + t^{2}}{y^{2} + t^{2}}} \frac{\cos(x)}{y \, Q x \, dy};$$

$$C_{1}^{ND} = Q^{2} \frac{x \, dx}{x \, dx} \frac{y \, dy}{y \, dy} d \frac{p \frac{t}{t^{2} + y^{2}}}{p \frac{t^{2} + y^{2}}{t^{2} + y^{2}}} \frac{e^{\frac{d}{y} \cdot Q x \, dy}}{p \sqrt{y} \, Q x \, dy} 1 \frac{p \frac{t}{t^{2} + (Q x)^{2}}}{p \frac{t^{2} + (Q x)^{2}}} \frac{1 + p \frac{t}{t^{2} + (Q x)^{2}}}{t^{2} + (Q x)^{2}} \cos(x);$$

$$C_{2}^{D} = \frac{Q^{3}}{2} \int_{0}^{2} x \, dx \int_{0}^{2} y \, dy \int_{0}^{2} d Q^{2} \frac{p \frac{x}{t^{2} + (Q x)^{2}}}{p \frac{t^{2} + (Q x)^{2}}} \frac{p \frac{y}{t^{2} + (Q y)^{2}}}{p \frac{t^{2} + (Q y)^{2}}} \cos(x) + 1 + \frac{p \frac{t}{t^{2} + (Q y)^{2}}}{q \sqrt{y}} \frac{q \frac{e^{-d Q \, dy} x \, dy}{p \sqrt{y}} d \frac{e^{-d Q \, dy} x \, dy}{q \sqrt{y}} \frac{d e^{-d Q \, dy} x \, dy}{q \sqrt{y}} \frac{q \frac{e^{-d Q \, dy} x \, dy}{p \sqrt{y}} \frac{q \sqrt{y}}{q \sqrt{y}} \frac{q \sqrt{y}}$$

From this one can extract the leading and sub-leading terms in an expansion in powers of Q, the result is given in Eq. (7). Some useful expressions for performing the expansion are provided in Appendix D.

## 2. D oped case

The calculation for the doped system proceeds exactly as in the previous case but we must allow for the electron and hole pockets to have di erent size. For each electron (or hole) pocket of size  $Q_e$  ( $Q_h$ ) there is a contribution like that in Eq. (C1). The K 's are half of those in Eq. (C3), (C4) and (C5). But  $K_1^D$  is di erent for holes and electrons:

$$K_{1e=h}^{D} = \frac{1}{2} \frac{pp^{0}}{2E(p)E(p^{0})} \cos():$$
 (C8)

The contributions coming from the  $1\!=\!2$  are easy to obtain and can be encoded in a new contribution  $C_{\rm new}$  in Eq. (C 6), where

$$C_{new} = Q^2 R_0 (Q);$$
 (C9)

and  $R_0$  is given in Appendix D.

## APPENDIX D:COULOMB INTEGRALS

Let us de ne

$$R_{n}(Q) = \int_{0}^{Z_{1}} dx dy dy d = \frac{xy\cos(n)}{Q^{2}x^{2} + y^{2}} (2Qxy\cos(n))$$

Then one can show that up to 0  $(Q^{10})$ 

# APPENDIX E: APPROXIMATE TW O-BAND M ODELS

There are two reasons for constructing approximate two-band models. Firstly, on physical grounds the high-energy bands should not be very important for the low-energy properties of the system. Secondly, it is much easier to work with 2 2 m atrices instead of 4 4 m atrices. In this appendix we derive the low-energy elective model by doing degenerate second order perturbation theory. The quality of the expansion is good as long as  $v_F p = t_2$ .

## 1. Sim ple low -energy m odel

If we transform the H am iltonian matrix in Eq. (3) by taking the symmetric and anti-symmetric combinations of the stand third rows (and columns) we can write  $H_{kin} = H_0 + H_1$ , where

$$H_{0} = \begin{bmatrix} 0 & t_{0} & 0 & 0 & 0^{1} \\ B & 0 & 0 & 0 & 0C \\ 0 & 0 & t_{2} & 0^{A} \\ 0 & 0 & 0 & 0 \end{bmatrix}$$
(E1)

$$H_{1} = \frac{1}{p - \frac{1}{2}} \begin{bmatrix} 0 & pe^{i(p)} & 0 & pe^{i(p)} \\ B & pe^{i(p)} & 0 & pe^{i(p)} \\ 0 & pe^{i(p)} & 0 & pe^{i(p)}A \\ pe^{i(p)} & 0 & pe^{i(p)} \\ \end{bmatrix}$$
(E2)

Perform ing second order perturbation theory one nds an e ective H am iltonian matrix,  $H_e = H_1^y (1=H_0)H_1$ , where:

$$H_{e} = \frac{p^{2}}{t_{2}} \begin{bmatrix} 0 & 0 & 0 & 0 \\ B & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 \\ 0 & e^{2i} & (p) \\ 0 & 0 & 0 \end{bmatrix} (E3)$$

The low-energy spinors are then given by:

$$(p) = \frac{1}{p - \frac{1}{2}} \begin{bmatrix} B & e^{i(p)} \\ 0 & A \\ 0 & A \end{bmatrix}; \quad (E 4)$$

and the corresponding energies are  $p^2 = t_2$ . If we add the contribution from  $_3$  (which is already diagonal in this basis) and only keep the B-atom components we in m ediately arrive at Eq. (10).

In fact it is easier to see the existence of the exchange instability in this basis. W orking in this subspace we again get an expression like that in Eq. (C1) with  $K_1^{D} = 0, K_1^{ND} = \cos(2), K_2^{D} = 1 \text{ and } K_2^{ND} = \cos(2)$ . If one further neglects the di erence between  $V^{D}$  and  $V^{ND}$  the resulting change in the exchange energy can be expressed with the help of the functions de ned in Appendix D. Explicitly the leading term in the exchange energy is /  $Q^3 R_0(1) + R_2(1) + 2Q^2 R_2(Q)$   $8Q^3=27$  in agreem ent with the result in Eq. (7).

# 2. M ore general low -energy m odel

A more general H am iltonian model for the low energy physics is given by<sup>3</sup>:

$$H_{0} = \begin{bmatrix} 0 & & & & & & & 1 \\ 0 & v_{F} p e^{i} & t_{?} & v_{4} p e^{i} & \\ B & v_{F} p e^{i} & 0 & v_{4} p e^{i} & v_{3} p e^{i} & \\ C & t_{?} & v_{4} p e^{i} & 0 & v_{F} p e^{i} & \\ v_{4} p e^{i} & v_{3} p e^{i} & v_{F} p e^{i} & 0 \end{bmatrix}$$
(E5)

O ne can perform a unitary transform ation so that H  $_2$  = M  $^{\rm y}{\rm H}_0{\rm M}$ , where M = M  $_1$  (p)M  $_2$  and M  $_1$  (p) and M  $_2$  are given in Eq. (A1) and (A2). We may then separate the transform ed H am iltonian into three parts, H  $_2$  = K  $_0+$  K  $_1+$  K  $_2$ , with:

$$K_{0} = \begin{bmatrix} 0 & t_{?} & 0 & 0 & 0^{1} \\ B & 0 & 0 & 0 & 0C \\ 0 & 0 & t_{?} & 0^{A} \end{bmatrix};$$
(E6)  

$$K_{1} = \begin{bmatrix} 0 & v_{3}p\cos(3) & 0 & i_{M}p\sin(3) \\ 0 & 0 & 0 & 0 \end{bmatrix} \\K_{1} = \begin{bmatrix} 0 & 0 & v_{3}p\cos(3) & 0 & i_{M}p\sin(3) \\ 0 & 0 & 0 & 0 \end{bmatrix} \\K_{2} = \begin{bmatrix} (v_{F} + v_{4})p & 0 & 0 & 0 \\ 0 & 0 & 0 & (v_{F} + v_{4})p \end{bmatrix} \\K_{2} = \begin{bmatrix} (v_{F} + v_{4})p & 0 & 0 & 0 \\ 0 & 0 & 0 & (v_{F} & v_{4})p \end{bmatrix} \\K_{2} = \begin{bmatrix} (v_{F} + v_{4})p & 0 & 0 & 0 \\ 0 & 0 & 0 & (v_{F} & v_{4})p \end{bmatrix} \\K_{2} = \begin{bmatrix} 0 & (v_{F} + v_{4})p & 0 & 0 & 0 \\ 0 & 0 & (v_{F} & v_{4})p & 0 \end{bmatrix}$$

W ith this decomposition it is easy to not the approximate eigenstates and eigenvalues for  $v_F p = t_2$ .

For the high-energy states one can use the simple non-degenerate perturbation theory. The eigenvalues are given by  $E_3 = t_2 + (v_F + v_4)^2 p^2 = t_2$  and  $E_4 = t_2 + (v_F - v_4)^2 p^2 = t_2$ . It is also straightforward to obtain the corresponding states. For the low energy sector the second order perturbation result (from two K<sub>2</sub> and one K<sub>0</sub>) can give a term which is of the same order as that of K<sub>1</sub>. Thus, we must use degenerate perturbation theory. The usualmanipulations then given the Ham iltonian matrix in the low energy subspace as K<sub>low</sub> = K<sub>1</sub> = K<sub>2</sub>P<sub>1</sub> (1=K<sub>0</sub>)P<sub>1</sub>K<sub>2</sub>, where P<sub>1</sub> is the projection out of the low-energy subspace, explicitly

$$K_{low} = \begin{pmatrix} 0 & 0 & 0 & 1 & 0 & 0 & 0 & 1 \\ B & 0 & v_3 p \cos(3) & 0 & i v_3 p \sin(3) C & p^2 B & 0 & (v_F + v_4)^2 & 0 & 0 & C \\ 0 & 0 & 0 & 0 & A + \frac{p^2}{t_2} B & 0 & (v_F + v_4)^2 & 0 & 0 & C \\ 0 & i v_3 p \sin(3) & 0 & v_3 p \cos(3) & 0 & 0 & 0 & (v_F - v_4)^2 \end{pmatrix}$$
(E9)

and the corresponding eigenvalues are

$$\frac{2v_{\rm F} v_4 p^2}{t_2} \qquad (v_3 p)^2 + \frac{h}{t_2} \frac{(v_{\rm F}^2 + v_4^2) p^2}{t_2} \frac{i_2}{2 (v_3 p)} \frac{h}{t_2} \frac{(v_{\rm F}^2 + v_4^2) p^2}{t_2} \frac{i}{\cos(3)} \qquad (E10)$$

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